

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor IRF250P225, IIRF250P225

• FEATURES

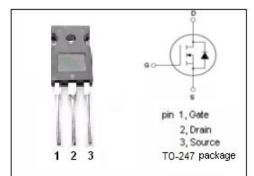
- Static drain-source on-resistance: $R_{DS}(on) \leqslant 22m_{\Omega}$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

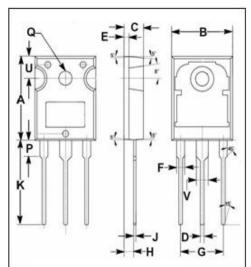
DESCRITION

· OR-ring and redundant power switches

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	250	V			
V _{GS}	Gate-Source Voltage	±20				
lD	Drain Current-Continuous	69	A			
I _{DM}	Drain Current-Single Pulsed	276	A			
PD	Total Dissipation @Tc=25°C	313	W			
Tj	Max. Operating Junction Temperature	175	°C			
T _{stg}	Storage Temperature	-55~175	°C			







• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(j-c)	Channel-to-case thermal resistance	0.48	°C /W
Rth(j-a)	th(j-a) Channel-to-ambient thermal resistance		°C/W

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ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	250			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I₀=270 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =41A			22	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = 20V			0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =200V; V _{GS} = 0V			1.0	μA
Vsd	Diode forward voltage	I _S =41A, V _{GS} = 0V			1.2	V

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